



### General Description

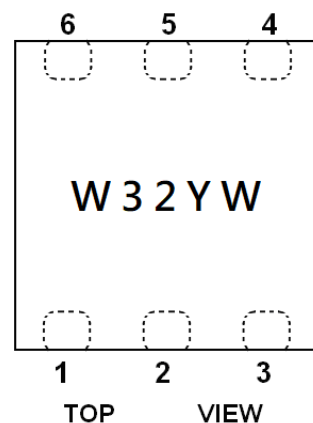
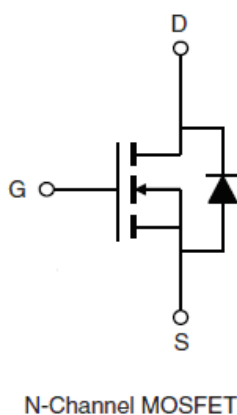
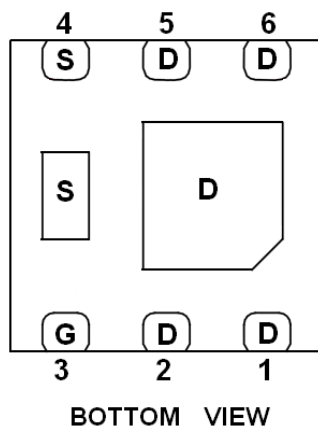
AFN2432WS, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- $I_D=6.2A, R_{DS(ON)}=25m\Omega@V_{GS}=10V$
- $I_D=5.2A, R_{DS(ON)}=38m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- DFN2X2-6L package design

### Pin Description ( DFN2X2-6L )



### Application

- DC/DC Converter
- High Frequency Switching

### Pin Define

Pin	Symbol	Description
1,2,5,6	D	Drain
4	S	Source
3	G	Gate

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN2432WSFN226RG	W32YW	DFN2X2-6L	Tape & Reel	4000 EA

- ※ W32 part code
- ※ Y year code
- ※ W week code
- ※ AFN2432WSFN226RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	6.2
		T <sub>A</sub> =70°C	4.2
Pulsed Drain Current	I <sub>DM</sub>	20	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	2.8	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	3.5
		T <sub>A</sub> =70°C	2.2
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	36	°C/W

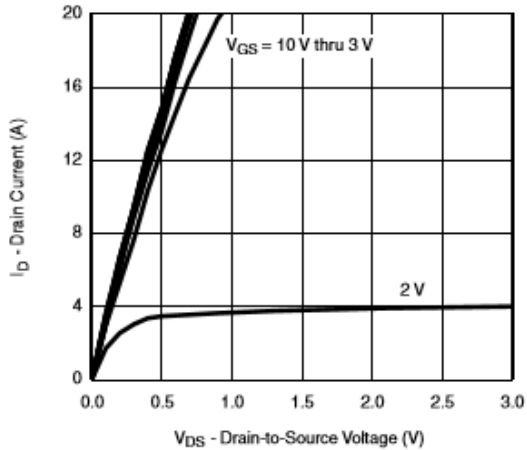
**Electrical Characteristics**

(T<sub>A</sub>=25°C Unless otherwise noted)

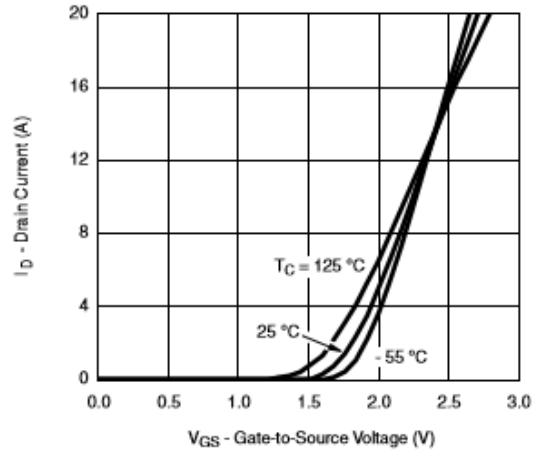
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.1		2.1	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =10V	20			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.2A		20	25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.2A		30	38	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =6.1A		20		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2.0A, V <sub>GS</sub> =0V		0.8	1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≧7.8A		7	11	nC
Gate-Source Charge	Q <sub>gs</sub>			2		
Gate-Drain Charge	Q <sub>gd</sub>			1.7		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1MHz		650		pF
Output Capacitance	C <sub>oss</sub>			115		
Reverse Transfer Capacitance	C <sub>rss</sub>			45		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =2.4Ω I <sub>D</sub> ≧6.2A, V <sub>GEN</sub> =10V R <sub>G</sub> =1Ω		10	20	ns
	t <sub>r</sub>			10	20	
Turn-Off Time	t <sub>d(off)</sub>			20	40	
	t <sub>f</sub>			10	20	



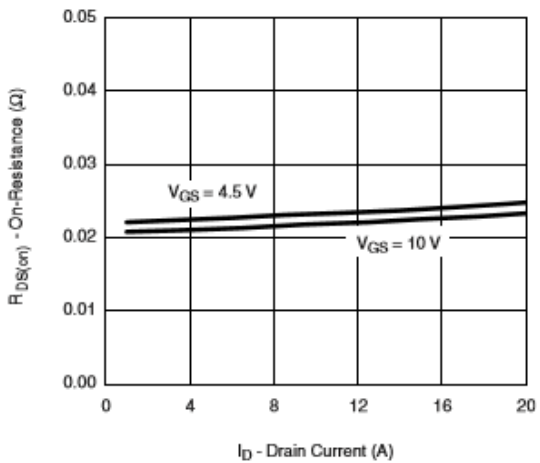
## Typical Characteristics



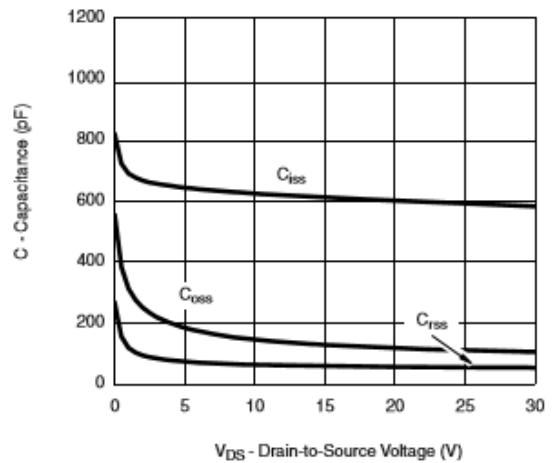
Output Characteristics



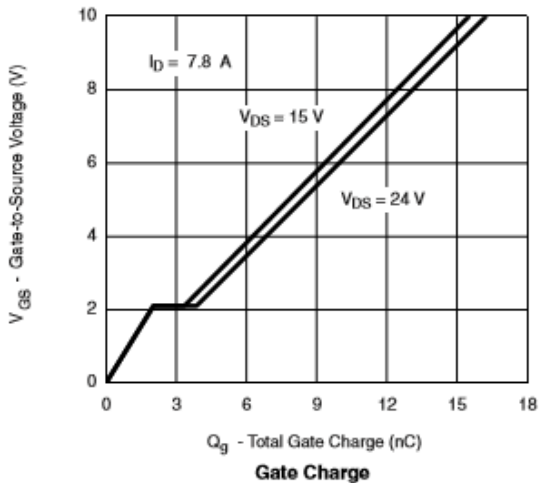
Transfer Characteristics



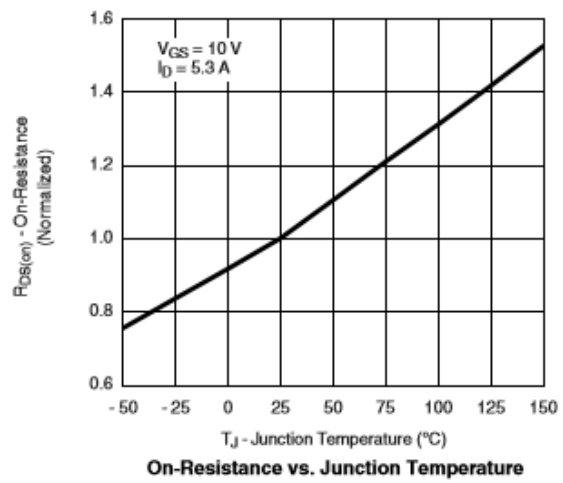
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



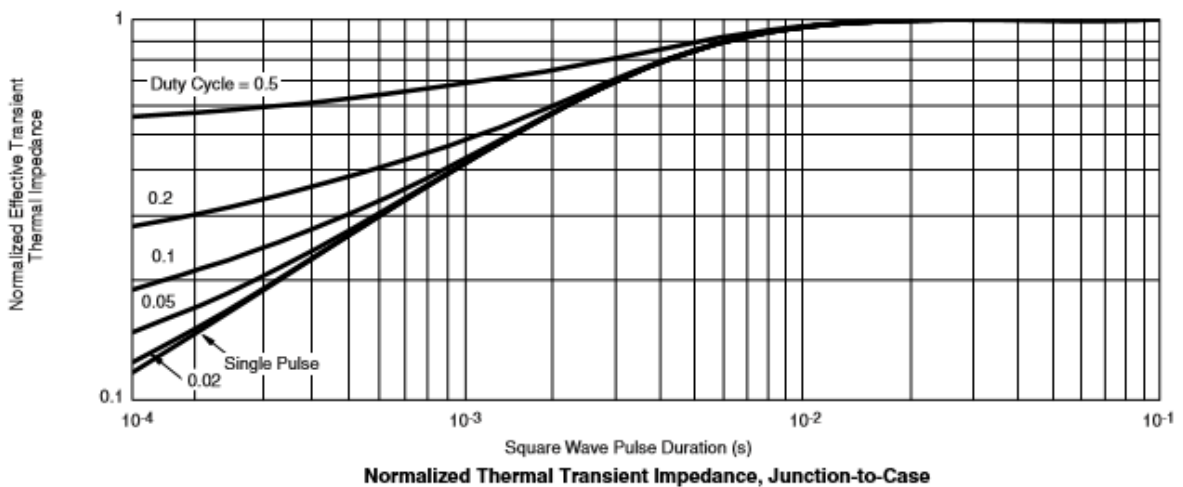
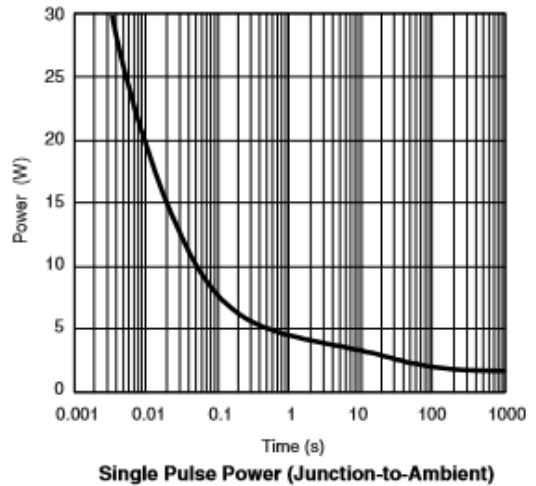
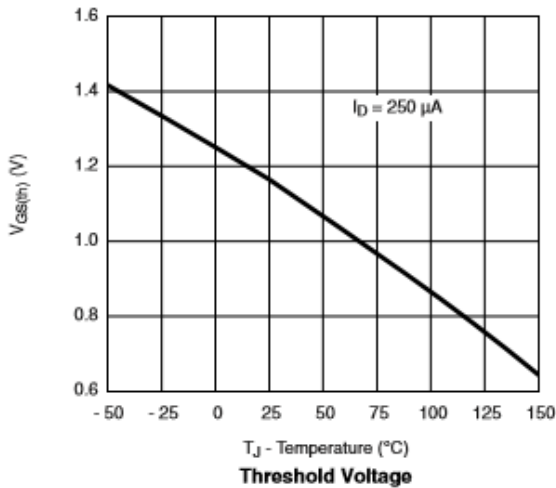
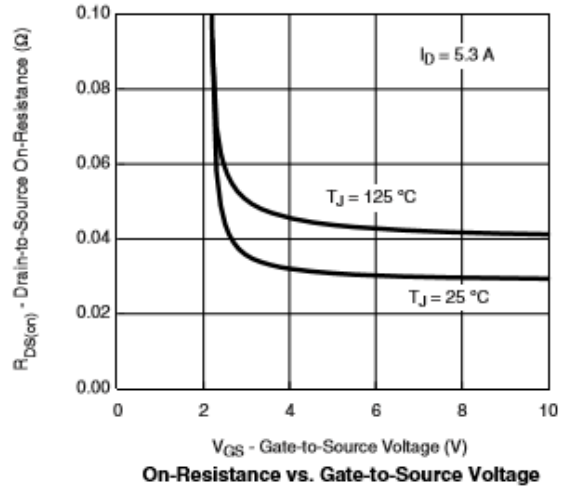
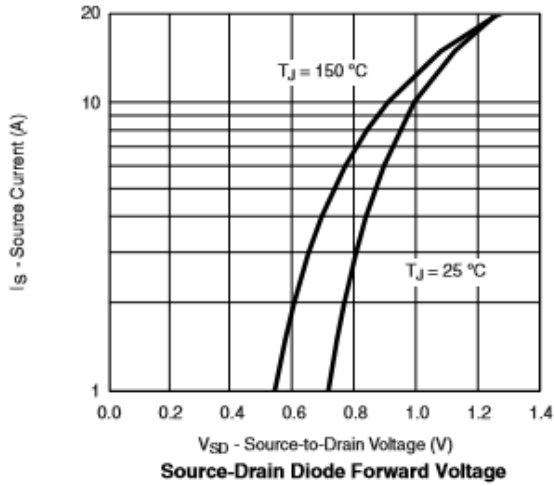
Gate Charge



On-Resistance vs. Junction Temperature



## Typical Characteristics





**Typical Characteristics**

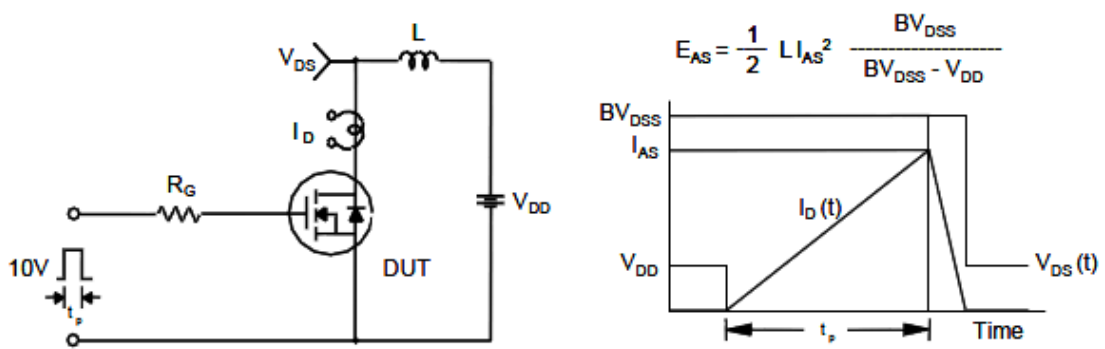
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

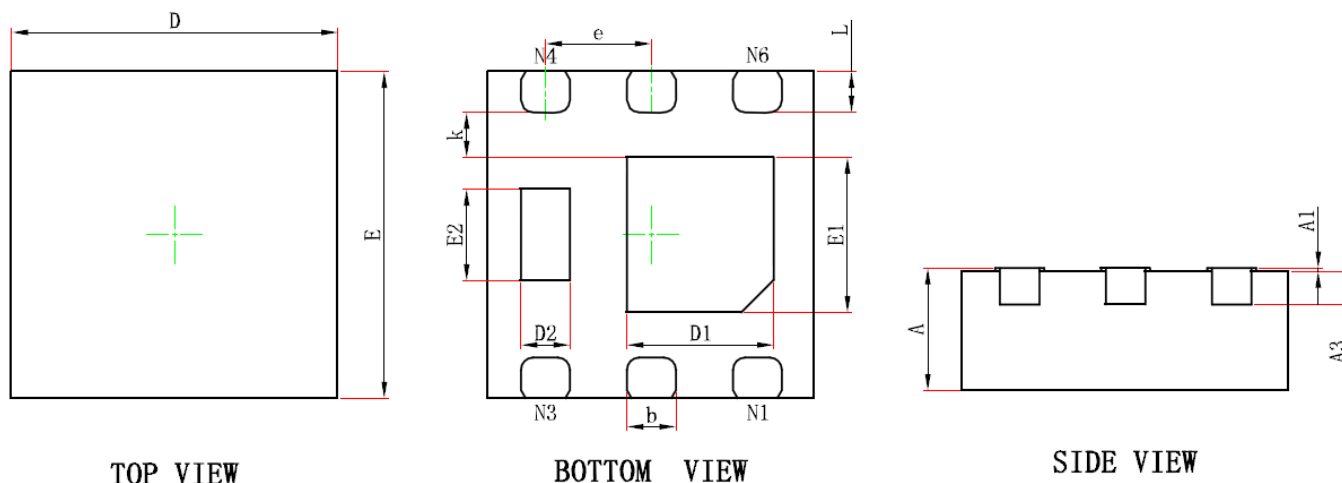


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( DFN2X2-6L )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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